

# **STTH1002C-Y**

# Automotive high efficiency ultrafast diode

#### **Features**

- Suited for SMPS
- Low losses
- Low forward and reverse recovery times
- High junction temperature
- Low leakage current
- AEC-Q101 qualified

## **Description**

Dual center tap rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in DPAK and D<sup>2</sup>PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection for automotive applications.

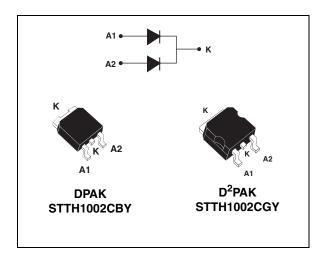


Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	Up to 2 x 8 A
$V_{RRM}$	200 V
T <sub>j</sub> (max)	175 °C
V <sub>F</sub> (typ)	0.78 V
t <sub>rr</sub> (typ)	20 ns

Characteristics STTH1002C-Y

### 1 Characteristics

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter	Value	Unit			
$V_{RRM}$	Repetitive peak reverse voltage			200	V	
D <sup>2</sup> PAK				20	Α	
I <sub>F</sub> (RMS)	Forward rms current		DPAK	10	A	
	Avarage forward current $\delta = 0.5$	T <sub>c</sub> = 155 °C	Per diode	5	А	
,		T <sub>c</sub> = 150 °C	Per device	10		
I <sub>F(AV)</sub>		T <sub>c</sub> = 135 °C	Per diode	8		
		T <sub>c</sub> = 125 °C		16		
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			50	Α	
T <sub>stg</sub>	Storage temperature range			-65 to + 175	°C	
Tj	Operating junction temperature range			-40 to + 175	°C	

Table 3. Thermal parameters

Symbol	Parameter	Value (max)	Unit
B	Junction to case Per diode	4.0	
R <sub>th(j-c)</sub>	Per device	2.5	°C/W
R <sub>th(j-c)</sub>	Coupling	1.0	

When the diodes 1 and 2 are used simultaneously:  $\Delta T_j$  (diode1) = P(diode1) x R<sub>th(j-c)</sub> (per diode) + P(diode2) x R<sub>th(c)</sub>

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	Povorco logicado ourrent	T <sub>j</sub> = 25 °C	V - V		5	μΑ	
	T <sub>j</sub> = 125 °C	$V_R = V_{RRM}$		3	40		
V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A			1.1		
	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10 A			1.25	V	
	Torward voltage drop	T <sub>j</sub> = 150 °C	I <sub>F</sub> = 5 A		0.78	0.89	V
		T <sub>j</sub> = 150 °C	I <sub>F</sub> = 10 A			1.05	

<sup>1.</sup> Pulse test:  $t_p$  = 5 ms,  $\delta$  < 2 %

To evaluate the conduction losses use the following equation:

$$P = 0.73 \text{ x } I_{F(AV)} + 0.032 I_{F}^{2}_{(RMS)}$$

<sup>2.</sup> Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2 %

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 Table 5.
 Dynamic electrical characteristics

Symbol	Parameter	7	Min.	Тур.	Max.	Unit	
t <sub>rr</sub>	Reverse recovery time	,	$I_F = 1 \text{ A V}_R = 30 \text{ V}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$		20	25	ns
I <sub>RM</sub>	Reverse recovery current	T <sub>j</sub> = 125 °C	$I_F = 5 \text{ A}$ $V_R = 160 \text{ V}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$		5.9	7.6	Α
t <sub>fr</sub>	Forward recovery time	T <sub>j</sub> = 25 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$			110	ns
V <sub>FP</sub>	Forward recovery voltage	T <sub>j</sub> = 25 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$		2.4		V

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Figure 1. Peak current versus duty cycle (per diode)

I<sub>M</sub>(A) 40 30 P = 10W 20  $\delta = tp/T$ 10 0.1 0.3 0.4 0.5 0.6 0.7 0.0

Figure 2. Forward voltage drop versus forward current (typical values, per diode)

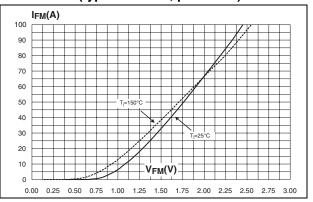


Figure 3. Forward voltage drop versus forward current (maximum values, per diode)

I<sub>FM</sub>(A) 100 90 80 70 50 40 30 20 0.00 0.25 0.50 0.75 1.00 1.25 1.50 1.75 2.00 2.25 2.50 2.75 3.00

Figure 4. **Relative variation of thermal** impedance junction to case versus pulse duration

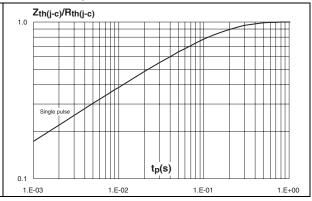
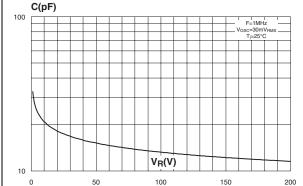
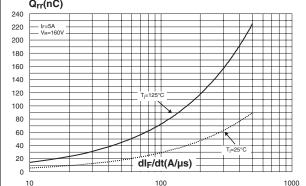


Figure 5. Junction capacitance versus reverse voltage applied

Figure 6. Reverse recovery charges versus dl<sub>F</sub>/dt (typical values, per diode) (typical values, per diode) Q<sub>rr</sub>(nC) 240 F=1MHz 220 I<sub>F</sub>=5A V<sub>R</sub>=160V 200





STTH1002C-Y Characteristics

Figure 7. Reverse recovery time versus dl<sub>F</sub>/dt Figure 8. (typical values, per diode)

#### Peak reverse recovery current versus dl<sub>F</sub>/dt (typical values, per diode)

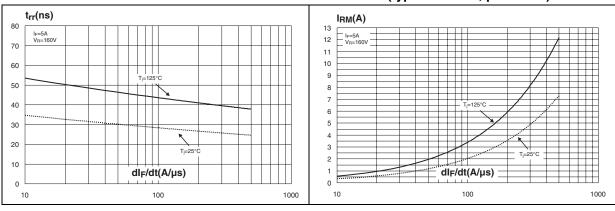


Figure 9. Dynamic parameters versus junction temperature

Figure 10. Thermal resistance junction to ambient versus copper surface under tab for D<sup>2</sup>PAK

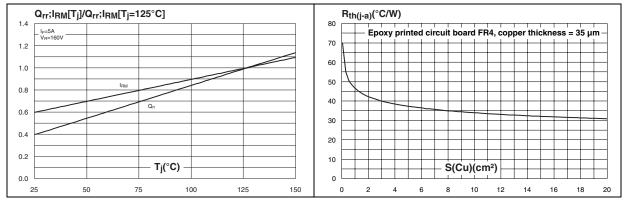
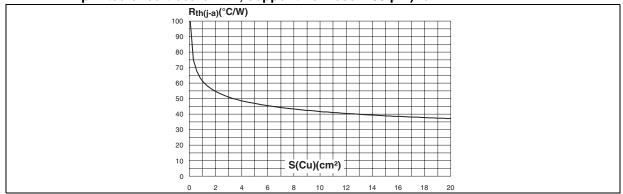


Figure 11. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness = 35 µm) for DPAK

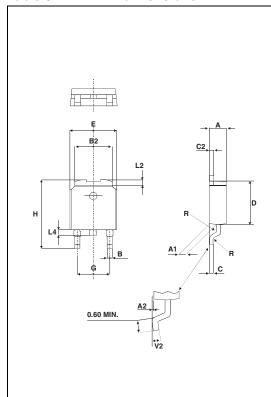


## 2 Package mechanical data

- Epoxy meets UL94, V0
- Cooling method: by conduction (method C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Table 6. DPAK dimensions



		nsions	sions		
Ref.	Ref. Millimete		eters Incl		
	Min.	Max.	Min.	Max.	
Α	2.20	2.40	0.086	0.094	
A1	0.90	1.10	0.035	0.043	
A2	0.03	0.23	0.001	0.009	
В	0.64	0.90	0.025	0.035	
B2	5.20	5.40	0.204	0.212	
С	0.45	0.60	0.017	0.023	
C2	0.48	0.60	0.018	0.023	
D	6.00	6.20	0.236	0.244	
Е	6.40	6.60	0.251	0.259	
G	4.40	4.60	0.173	0.181	
Н	9.35	10.10	0.368	0.397	
L2	0.80 typ.		0.03	1 typ.	
L4	0.60	1.00	0.023	0.039	
V2	0°	8°	0°	8°	

Figure 12. Footprint (dimensions in mm)

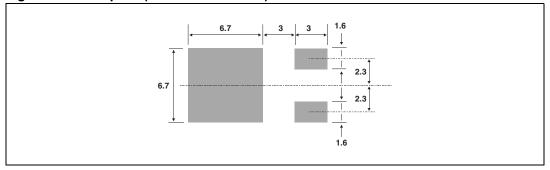


Table 7. D<sup>2</sup>PAK dimensions

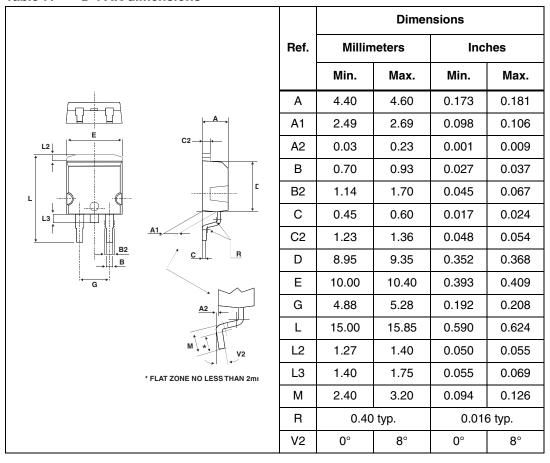
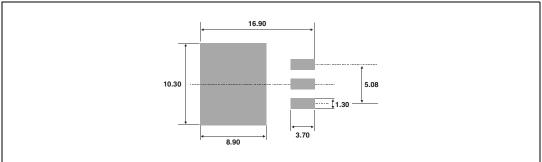


Figure 13. Footprint (dimensions in mm)



Ordering information STTH1002C-Y

# 3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH1002CBY-TR	STTH1002CY	DPAK	0.3 g	2500	Tape and reel
STTH1002CGY-TR	STTH1002CGY	D <sup>2</sup> PAK	1.48 g	1000	Tape and reer

# 4 Revision history

Table 9. Document revision history

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Date	Revision	Changes
21-Oct-2010	1	First issue.
03-Nov-2011	2	Updated Table 7 and Table 8.

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